

a1 second metallic layer, and said first metallic layer has a smaller area than a bottom area of the semiconductor element.

---

5. (Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming an electrodeposition frame on a flexible flat metallic substrate, said electrodeposition frame having first metallic layers and second metallic layers for external extension being patterned, wherein said first metallic layers are thicker than said second metallic layers;

a2 contiguously mounting a plurality of semiconductor elements, each with electrode pads thereon, on said first metallic layers;

wire-bonding the electrode pads to said second metallic layers which are located between said semiconductor elements;

resin-sealing said semiconductor elements mounted on said electrodeposition frame;

removing said metallic substrate to provide a resin sealing body; and

cutting said resin sealing body into individual semiconductor devices, wherein each device is provided with the first and second metallic layers.

---

Please add new claim 9 as follows:

a3 9. A semiconductor device according to claim 1, wherein the thickness of each of said first metallic layer and said second metallic layer is between about 20  $\mu\text{m}$  and about 35  $\mu\text{m}$  (micrometers).

---

#### IN THE DRAWINGS

Submitted herewith under separate cover is a Request for Approval of Drawing Amendments to which is attached a photocopy of Figure 8 with proposed corrections in red ink.

#### REMARKS

The Office Action of May 23, 2002 has been thoroughly studied. Accordingly, the changes presented herein for the application, considered together with the following remarks, are believed to be sufficient to place the application into condition for allowance.